

**AMENDMENTS TO THE SPECIFICATION:**

**On page 1 after the title, add the following paragraph:**

**Cross Reference to Related Application**

This application is a continuation of U.S. Application Serial No. 09/380,322, filed August 30, 1999.

**Please amend the paragraph beginning on page 6, line 4 as follows:**

Therefore, the purpose of the invention is a process for the transfer of at least one thin film of solid material delimited in an initial substrate, characterized in that it comprises the following steps:

- a step in which a layer of inclusions is formed in the initial substrate at a depth corresponding to the required thickness of the thin film, these inclusions being designed to form traps for gaseous compounds which will subsequently be implanted;

- a subsequent step for implantation of the said gaseous compounds, in a manner to convey the gaseous [species] compounds into the layer of inclusions, the dose of implanted gaseous compounds being sufficient to cause the formation of micro-cavities likely to form a fracture plane along which the thin film can be separated from the remainder of the substrate.

**Please amend the paragraph beginning on page 6, line 22 as follows:**

The step of implanting gaseous [species] compounds can be carried out with an implantation energy of these gaseous [species] compounds that is such that their mean depth of penetration into the substrate corresponds to the depth of the layer of inclusions. It can also be carried out with an implantation energy of these gaseous [species] compounds that is such that their mean depth of penetration into the substrate is close to the layer of inclusions, this

implantation being associated with a diffusion heat treatment to allow the migration of the implanted [species] compounds to the layer of inclusions.

**HAYES SOLOWAY P.C.**

130 W. CUSHING ST.  
TUCSON, AZ 85701  
TEL. 520.882.7623  
FAX. 520.882.7643

175 CANAL STREET  
MANCHESTER, NH 03101  
TEL. 603.668.1400  
FAX. 603.668.8567